

# PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2000-228527

(43)Date of publication of application : 15.08.2000

(51)Int.Cl.

H01L 29/786

H01L 21/336

(21)Application number : 11-345498

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(22)Date of filing : 03.12.1999

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(30)Priority

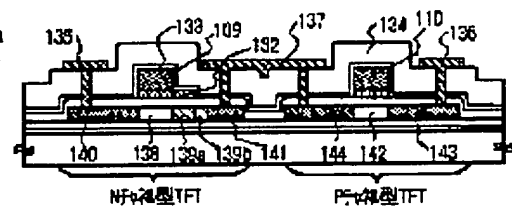
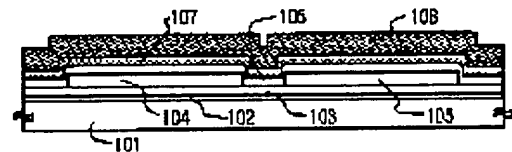
Priority number : 10344746 Priority date : 03.12.1998 Priority country : JP

## (54) SEMICONDUCTOR DEVICE AND MANUFACTURE THEREOF

(57)Abstract:

**PROBLEM TO BE SOLVED:** To obtain good characteristics in both states of ON and OFF, by allowing a gate electrode to have the first and second layers, a semiconductor layer to have a channel forming region, a first and second impurity regions, and a part 1 of the second impurity region to be overlaid with the first layer of the gate electrode.

**SOLUTION:** A first conductive film 107 to be the first layer of a gate electrode and a second conductive layer 108 to be the second layer of the gate electrode are formed on the surface of a gate insulating film 106. The first conductive film 107 is a semiconductor film containing Si or Ge as a main component. The second conductive film 108 contains Ti, Ta, W and Mo as main components. A channel forming region 138, first impurity regions 140, 141 and a second impurity region are formed in an n-channel TFT (a thin film transistor) of a CMOS circuit. Here, in the second impurity region, a region 139a (GOLD region) which superimposes with the gate electrode and a region 139b (LDD region) which does not overlap the gate electrode are respectively formed.



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[Date of request for examination]  
[Date of sending the examiner's decision of rejection]  
[Kind of final disposal of application other than the examiner's  
decision of rejection or application converted registration]  
[Date of final disposal for application]  
[Patent number]  
[Date of registration]  
[Number of appeal against examiner's decision of rejection]  
[Date of requesting appeal against examiner's decision of  
rejection]  
[Date of extinction of right]

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